



SOT-23 Plastic-Encapsulate Diodes

CMPSH-3/3A/3C/3S SCHOTTKY DIODE

FEATURES

Power dissipation

$$P_D : 350 \text{ mW (Tamb=25)}$$

Forward Current

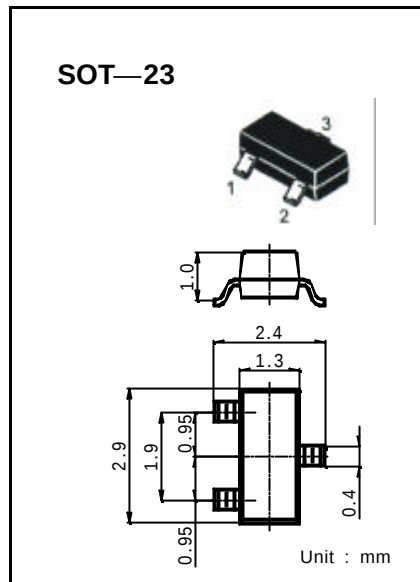
$$I_F : 100 \text{ mA}$$

Reverse Voltage

$$V_R : 30 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55 \text{ to } +150$$

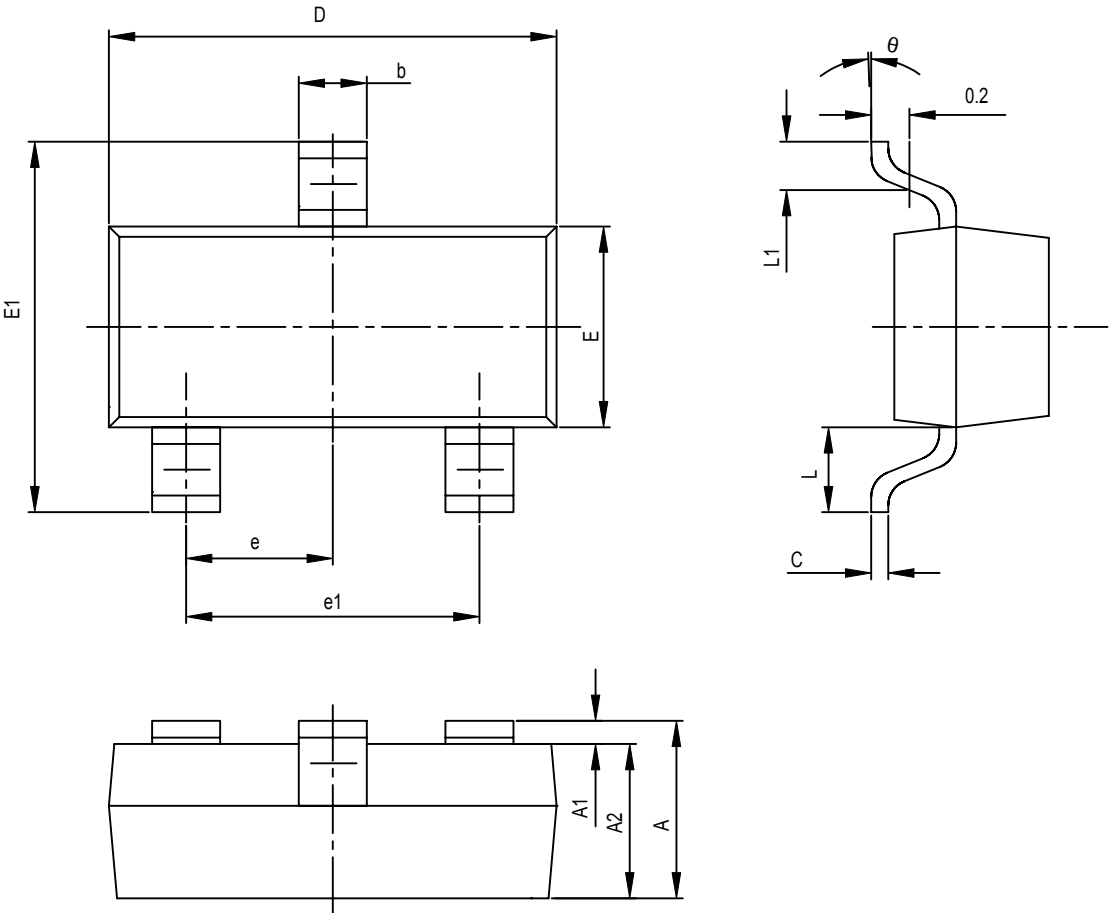


CMPSH-3 Marking: D95 CMPSH-3A Marking: DB1 CMPSH-3C Marking: DB2 CMPSH-3S Marking: DA5

ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100 \mu A$	30		V
Reverse voltage leakage current	I_R	$V_R = 25V$ $V_R = 25V, T_A = 100$		500	nA
				100	μA
Forward voltage	V_F	$I_F = 2mA$		0.33	V
		$I_F = 15mA$		0.45	
		$I_F = 100mA$		1	
Diode capacitance	C_{tot}	$V_R = 0V$ $f = 1MHz$		8	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{RR} = 1.0mA$ $R_L = 100 \Omega$		5	ns

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TPY		0.037TPY	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°